Quad Analog Switch/Quad Multiplexer

The MC14066B consists of four independent switches capable of controlling either digital or analog signals. This quad bilateral switch is useful in signal gating, chopper, modulator, demodulator and CMOS logic implementation.

The MC14066B is designed to be pin-for-pin compatible with the MC14016B, but has much lower ON resistance. Input voltage swings as large as the full supply voltage can be controlled via each independent control input.

Features

- Triple Diode Protection on All Control Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Linearized Transfer Characteristics
- Low Noise 12 nV/ $\sqrt{\text{Cycle}}$, $f \ge 1.0$ kHz typical
- Pin-for-Pin Replacement for CD4016, CD4016, MC14016B
- For Lower R_{ON}, Use The HC4066 High-Speed CMOS Device
- Pb-Free Packages are Available

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V _{in} , V _{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to V _{DD} + 0.5	V
l _{in}	Input Current (DC or Transient) per Control Pin	±10	mA
I _{SW}	Switch Through Current	±25	mA
P _D	Power Dissipation, per Package (Note 1)	500	mW
T _A	Ambient Temperature Range	-55 to +125	°C
T _{stg}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8-Second Soldering)	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Temperature Derating:

Plastic "P and D/DW" Packages: - 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

1



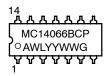
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



PDIP-14 P SUFFIX **CASE 646**



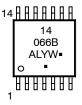


SOIC-14 **D SUFFIX CASE 751A**



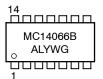


TSSOP-14 **DT SUFFIX** CASE 948G





SOEIAJ-14 **F SUFFIX CASE 965**



= Assembly Location

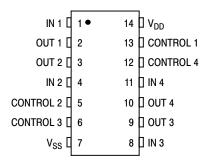
= Wafer Lot WI I YY. Y = Year = Work Week WW, W = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

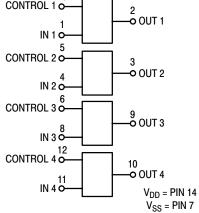
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

PIN ASSIGNMENT



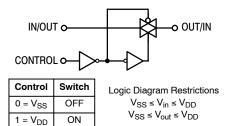
CONTROL 1 13 2

BLOCK DIAGRAM

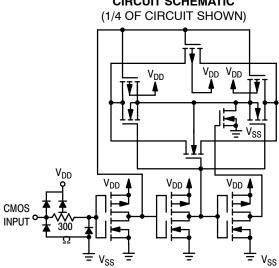


LOGIC DIAGRAM AND TRUTH TABLE

(1/4 OF DEVICE SHOWN)



CIRCUIT SCHEMATIC



ELECTRICAL CHARACTERISTICS

				- 5	5°C		25°C		12	5°C	
Characteristic	Symbol	V _{DD}	Test Conditions	Min	Max	Min	Typ ⁽²⁾	Max	Min	Max	Unit
SUPPLY REQUIREMENTS	(Voltages F	Referen	ced to V _{EE})		•	•	•	•	•	•	
Power Supply Voltage Range	V _{DD}	_		3.0	18	3.0	-	18	3.0	18	V
Quiescent Current Per Package	I _{DD}	5.0 10 15	$\begin{split} & \text{Control Inputs:} \\ & V_{\text{in}} = V_{\text{SS}} \text{ or } V_{\text{DD}}, \\ & \text{Switch I/O: } V_{\text{SS}} \leq V_{\text{I/O}} \\ & \leq V_{\text{DD}}, \text{ and} \\ & \Delta V_{\text{switch}} \leq 500 \text{ mV} \ ^{(3)} \end{split}$	- - -	0.25 0.5 1.0	- - -	0.005 0.010 0.015	0.25 0.5 1.0	- - -	7.5 15 30	μА
Total Supply Current (Dynamic Plus Quiescent, Per Package	I _{D(AV)}	5.0 10 15	T _A = 25°C only The channel component, (V _{in} – V _{out})/R _{on} , is not included.)		Typica	(0.2	97 μΑ/kHz) f 90 μΑ/kHz) f 96 μΑ/kHz) f	+ I _{DD}			μΑ
CONTROL INPUTS (Voltage	es Referenc	ced to \	V _{SS})								
Low-Level Input Voltage	V _{IL}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	V
High-Level Input Voltage	V _{IH}	5.0 10 15	R _{on} = per spec, I _{off} = per spec	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	V
Input Leakage Current	I _{in}	15	V _{in} = 0 or V _{DD}	-	± 0.1	_	±0.00001	± 0.1	-	± 1.0	μΑ
Input Capacitance	C _{in}	_		-	_	-	5.0	7.5	_	-	pF
SWITCHES IN AND OUT (V	oltages Re	ference	ed to V _{SS})								
Recommended Peak-to- Peak Voltage Into or Out of the Switch	V _{I/O}	_	Channel On or Off	0	V _{DD}	0	-	V _{DD}	0	V _{DD}	V _{p-p}
Recommended Static or Dynamic Voltage Across the Switch (3) (Figure 1)	ΔV_{switch}	-	Channel On	0	600	0	-	600	0	300	mV
Output Offset Voltage	V _{OO}	-	V _{in} = 0 V, No Load	-	_	_	10	-	-	-	μV
ON Resistance	R _{on}	5.0 10 15	$\begin{split} \Delta V_{\text{switch}} &\leq 500 \text{ mV }^{(3)}, \\ V_{\text{in}} &= V_{\text{IL}} \text{ or } V_{\text{IH}} \\ \text{(Control), and } V_{\text{in}} &= \\ 0 \text{ to } V_{DD} \text{ (Switch)} \end{split}$	- - -	800 400 220	- - -	250 120 80	1050 500 280	- - -	1200 520 300	Ω
ΔON Resistance Between Any Two Channels in the Same Package	ΔR_{on}	5.0 10 15		- - -	70 50 45	- - -	25 10 10	70 50 45	- - -	135 95 65	Ω
Off-Channel Leakage Current (Figure 6)	I _{off}	15	V _{in} = V _{IL} or V _{IH} (Control) Channel to Channel or Any One Channel	-	±100	_	± 0.05	±100	-	±1000	nA
Capacitance, Switch I/O	C _{I/O}	-	Switch Off	-	-	_	10	15	-	-	pF
Capacitance, Feedthrough (Switch Off)	C _{I/O}	_ _		-	-	-	0.47	-	_	-	pF

Data labeled "Typ" is not to be used for design purposes, but is intended as an indication of the IC's potential performance.
 For voltage drops across the switch (ΔV_{switch}) > 600 mV (> 300 mV at high temperature), excessive V_{DD} current may be drawn; i.e. the current out of the switch may contain both V_{DD} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded. (See first page of this data sheet.)

ELECTRICAL CHARACTERISTICS (Note 4) (C_L = 50 pF, T_A = 25°C unless otherwise noted.)

		V_{DD}				
Characteristic	Symbol	Vdc	Min	Typ ⁽⁵⁾	Max	Unit
Propagation Delay Times $V_{SS} = 0 \text{ Vdc}$ Input to Output (R _L = 10 k Ω)	t _{PLH} , t _{PHL}					ns
t_{PLH} , $t_{PHL} = (0.17 \text{ ns/pF}) C_L + 15.5 \text{ ns}$		5.0	_	20	40	
t_{PLH} , t_{PHL} = (0.08 ns/pF) C_L + 6.0 ns t_{PLH} , t_{PHL} = (0.06 ns/pF) C_L + 4.0 ns		10 15	-	10 7.0	20 15	
Control to Output ($R_L = 1 \text{ k}\Omega$) (Figure 2)	t _{PHZ}					ns
Output "1" to High Impedance		5.0	_	40	80 70	
		10 15	-	35 30	60	
Output "0" to High Impedance	t _{PLZ}	5.0	-	40	80	ns
		10 15	_ _	35 30	70 60	
High Impedance to Output "1"	t _{PZH}	5.0	_	60	120	ns
Tilgit impodation to Galpat	чи	10	_	20	40	110
		15	-	15	30	
High Impedance to Output "0"	t _{PZL}	5.0	-	60	120	ns
		10 15	_	20 15	40 30	
Construction Number of			_			0/
Second Harmonic Distortion $V_{SS} = -5 \text{ Vdc}$ ($V_{in} = 1.77 \text{ Vdc}$, RMS Centered @ 0.0 Vdc, $R_L = 10 \text{ k}\Omega$, f = 1.0 kHz)	-	5.0	_	0.1	_	%
$\begin{array}{ll} \mbox{Bandwidth (Switch ON) (Figure 3)} & \mbox{$V_{SS} = -5$ Vdc} \\ \mbox{$(R_L = 1$ k$\Omega, 20 Log ($V_{out}$/$V_{in}$) = -3$ dB, $C_L = 50$ pF,} \\ \mbox{$V_{in} = 5$ V_{p-p})} \end{array}$	-	5.0	-	65	-	MHz
$\label{eq:continuous} $	-	5.0	-	- 50	-	dB
	-	5.0	-	- 50	-	dB
Crosstalk, Control Input to Signal Output (Figure 5) $V_{SS} = -5 \text{ Vdc} \\ (R_1 = 1 \text{ k}\Omega, R_L = 10 \text{ k}\Omega, \text{ Control } t_{TLH} = t_{THL} = 20 \text{ ns})$	-	5.0	-	300	-	mV _{p-p}

^{4.} The formulas given are for the typical characteristics only at 25°C.
5. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

ORDERING INFORMATION

Device	Package	Shipping [†]
MC14066BCP	PDIP-14	
MC14066BCPG	PDIP-14 (Pb-Free)	25 Units / Rail
MC14066BD	SOIC-14	
MC14066BDG	SOIC-14 (Pb-Free)	55 Units / Rail
MC14066BDR2	SOIC-14	
MC14066BDR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC14066BDTR2	TSSOP-14*	1
MC14066BDTR2G	TSSOP-14*]
MC14066BF	SOEIAJ-14	
MC14066BFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC14066BFEL	SOEIAJ-14	
MC14066BFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb-Free.

TEST CIRCUITS

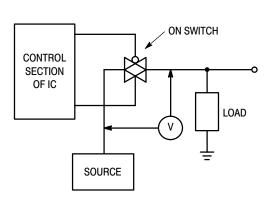


Figure 1. ΔV Across Switch

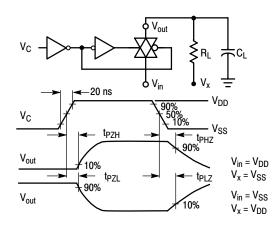


Figure 2. Turn-On Delay Time Test Circuit and Waveforms

 $V_C = V_{DD}$ FOR BANDWIDTH TEST $V_C = V_{SS}$ FOR FEEDTHROUGH TEST

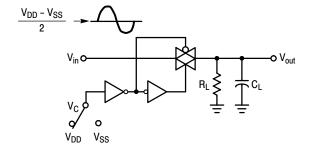


Figure 3. Bandwidth and Feedthrough Attenuation

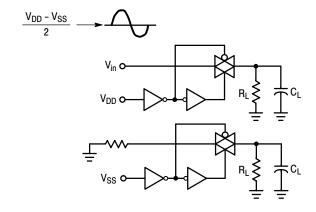


Figure 4. Channel Separation

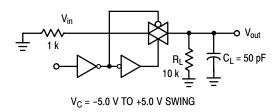


Figure 5. Crosstalk, Control to Output

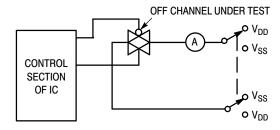


Figure 6. Off Channel Leakage

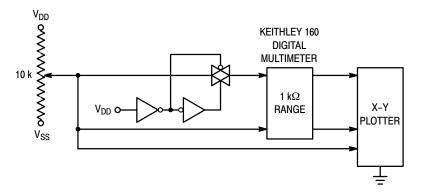


Figure 7. Channel Resistance (R_{ON}) Test Circuit

TYPICAL RESISTANCE CHARACTERISTICS

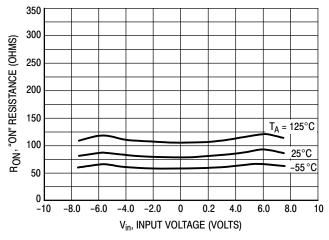


Figure 8. V_{DD} = 7.5 V, V_{SS} = - 7.5 V

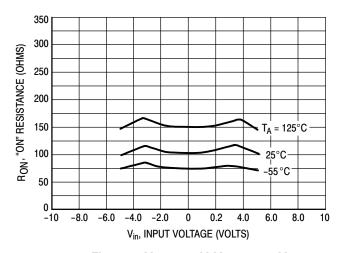


Figure 9. V_{DD} = 5.0 V, V_{SS} = - 5.0 V

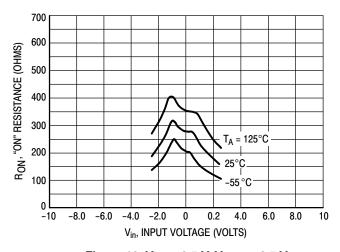


Figure 10. V_{DD} = 2.5 V, V_{SS} = - 2.5 V

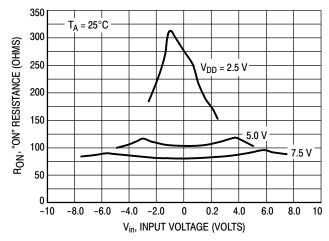


Figure 11. Comparison at 25°C, $V_{DD} = -V_{SS}$

APPLICATIONS INFORMATION

Figure A illustrates use of the Analog Switch. The 0-to-5 V digital control signal is used to directly control a 5 V peak-to-peak analog signal.

The digital control logic levels are determined by V_{DD} and V_{SS} . The V_{DD} voltage is the logic high voltage, the V_{SS} voltage is logic low. For the example, V_{DD} = + 5 V = logic high at the control inputs; V_{SS} = GND = 0 V = logic low.

The maximum analog signal level is determined by V_{DD} and V_{SS} . The analog voltage must not swing higher than V_{DD} or lower than V_{SS} .

The example shows a 5 V peak-to-peak signal which allows no margin at either peak. If voltage transients above

 V_{DD} and/or below V_{SS} are anticipated on the analog channels, external diodes (D_x) are recommended as shown in Figure B. These diodes should be small signal types able to absorb the maximum anticipated current surges during clipping.

The *absolute* maximum potential difference between V_{DD} and V_{SS} is 18 V. Most parameters are specified up to 15 V which is the *recommended* maximum difference between V_{DD} and V_{SS} .

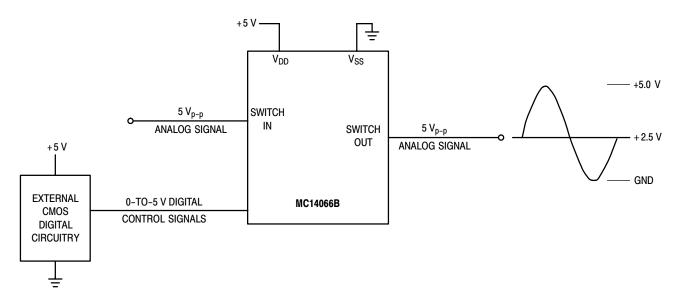


Figure A. Application Example

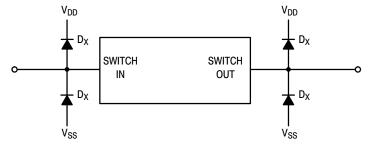
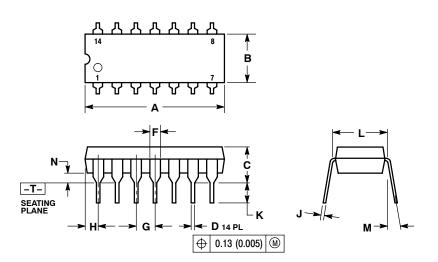


Figure B. External Germanium or Schottky Clipping Diodes

PACKAGE DIMENSIONS

PDIP-14 CASE 646-06 ISSUE P

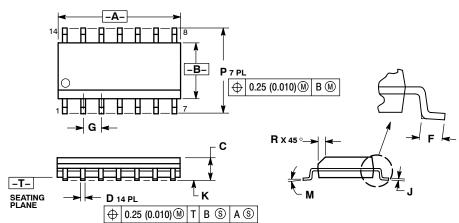


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.715	0.770	18.16	19.56		
В	0.240	0.260	6.10	6.60		
С	0.145	0.185	3.69	4.69		
D	0.015	0.021	0.38	0.53		
F	0.040	0.070	1.02	1.78		
G	0.100	BSC	2.54	2.54 BSC		
Н	0.052	0.095	1.32	2.41		
J	0.008	0.015	0.20	0.38		
K	0.115	0.135	2.92	3.43		
L	0.290	0.310	7.37	7.87		
М		10 °		10 °		
N	0.015	0.039	0.38	1.01		

PACKAGE DIMENSIONS

SOIC-14 CASE 751A-03 **ISSUE H**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

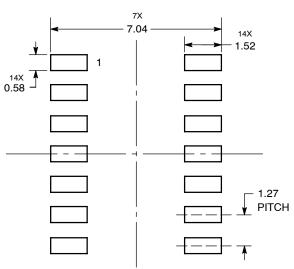
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7 °	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

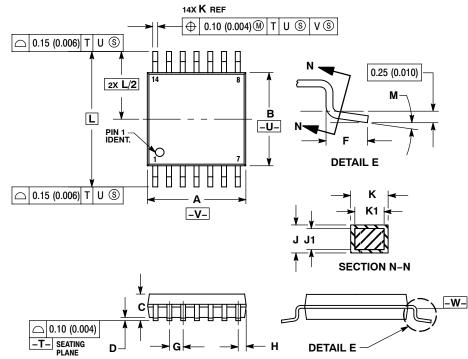


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

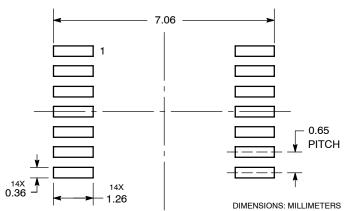
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL (0.003) TOTAL IN EACESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR
 REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	6.40 BSC 0.252 BS0		BSC
М	0 °	8 °	0 °	8 °

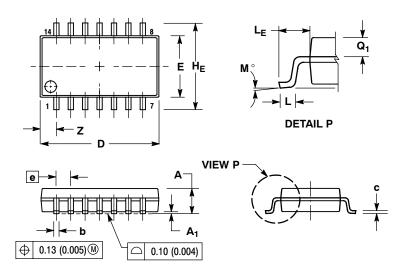
SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 **ISSUE A**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada

Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative